

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1944	((discharge near machin\$3) OR (PLASMA near discharge)) same (silicon or "SOI" near wafer)	USPAT; US-PGPU B; EPO; JPO; DERWEN T; IBM_TDB	2004/01/14 17:11
2	BRS	L2	77	1 same (dry near etch\$3)	USPAT; US-PGPU B; EPO; JPO; DERWEN T; IBM_TDB	2004/01/14 16:59
3	BRS	L3	43	2 and @pd<20010403	USPAT; US-PGPU B; EPO; JPO; DERWEN T; IBM_TDB	2004/01/14 17:02
4	BRS	L4	492	(discharge near machin\$3 or "EDM") same silicon	USPAT; US-PGPU B; EPO; JPO; DERWEN T; IBM_TDB	2004/01/14 17:17
5	BRS	L5	39	4 and (dry near etch\$3)	USPAT; US-PGPU B; EPO; JPO; DERWEN T; IBM_TDB	2004/01/14 17:17
6	BRS	L6	15	5 and @pd<20020228	USPAT; US-PGPU B; EPO; JPO; DERWEN T; IBM_TDB	2004/01/14 17:20
7	BRS	L8	4	7 and (discharge near machin\$3)	USPAT; US-PGPU B; EPO; JPO; DERWEN T; IBM_TDB	2004/01/14 17:24
8	BRS	L7	46	katakura-norihiro.in.	USPAT; US-PGPU B; EPO; JPO; DERWEN T; IBM_TDB	2004/01/14 17:21

	Type	L #	Hits	Search Text	DBs	Time Stamp
9	BRS	L9	9	7 and (reticle near blank)	USPAT; US-PGPU B; EPO; JPO; DERWEN T; IBM_TDB	2004/01/14 17:24